New Jersey Semi-Conductor Products, Inc.

20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A. 2N997

TELEPHONE: (973) 376-2922

(212) 227-6005

FAX: (973) 376-8960

N-P-N PLANAR SILICON TRANSISTOR

TWO TRIODES INTERNALLY CONNECTED

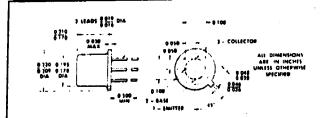
IN DARLINGTON CONFIGURATION

VERY HIGH GRAIN - 100MIN AT 100UA

LOW LEAKAGE – 10 NA MAX AT 60V

RUGGED INTERNAL CONNECTIONS

mechanical data



THE COLLECTOR IS IN ELECTRICAL CONTACT WITH THE CASE.

ALL JEDEC TO-18 DIMENSIONS AND NOTES ARE APPLICABLE.



*absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

	•																										
Collector-Base	Voltage														•											. 75	
Collector-Emit	ter Voltac	ze (Se	e N	Vote	1)																					. 40	٧
Emitter-Base	Voitage							٠		٠			•	•	•	٠	٠	•	•	•	•	•	•	٠		. /	٧
Collector Cur	rent			_																					30	iu m	a
Total Device D	Dissipation	at (c	r be	elow) 2	5°	C F	ree	-Ai	r Te	ewk	ere	atu	re (See	, N	ote	2)	,						,)) \	w
Total Device	Dissipation	at (c	or b	elow	v) 2	25°	C	Cas	e T	em	per	ratu	ıre	(Se	e i	Vot	e 3)			•		_	•		1.2 Y	₩
Storage Temp	erature F	lange		•			•		•	•	٠,	•	•	•	•	•	•	•	•	٠	- (55°(. to	, -	+ 3(70.4	C

*electrical characteristics at 25°C free-air temperature (unless otherwise noted)

	PARAMETER	T	EST CONDITIO	MIN	MAX	UNI	
BVCO	Collector-Base Breakdown Voltage	$I_{\rm C}=100~\mu a$,	le - · 0		75		V
BYCEO	Collector-Emitter Breakdown Voltage	1 _C 30 ma,	l ₉ 0,	(See Note 4)	40		v
BAEBO	Emitter-Base Breakdown Voltage	I _E == 100 μα,	lc == 0		7.		y
Iceo		V _{CB} = 60 v,	I _E = 0			10	na
	Collector Cutoff Current	V _{C8} = 60 v,	$I_{E}=0$,	T _A = 150°C		10	μο
ESO	Emitter Cutoff Current	$V_{EB} = 5 \text{ v},$	I _C = 0			10	no
h _{FE}		V _{CE} == 10 v,	$I_C = 100 \mu a$		1000		
		V _{CE} = 10 v,	I _C = 10 ma		4000		
	Static Forward Current Transfer Ratio	V _{CE} = 10 v,	$I_{\rm C}=100~{\rm ma}$,	(See Note 4)	7000	70,000	
		V _{CE} = 10 v, (See Note 4)	lc == 100 ma,	T _A = - 55°C	1000		
/ ₃₆	Base-Emitter Voltage	$V_{CE} = 10 v$	l _C = 100 ma,	(See Note 4)	0.9	18	٧
CE(sat)	Collector-Emitter Saturation Voltage	l _B ≈ 1 ma,	ł _c 10 0 ma,	(See Note 4)		16	٧



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